

Features

- Much lower Ron*A performance for On-state efficiency
- Better efficiency due to very low FOM

Applications

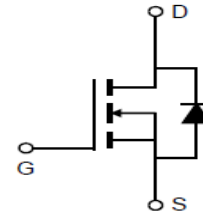
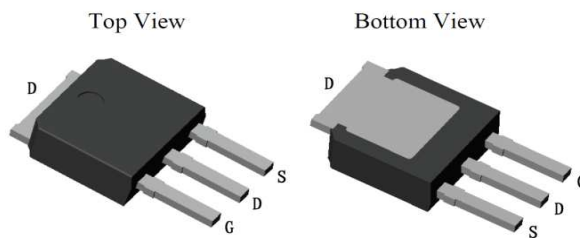
- LED/LCD/PDP TV and monitor Lighting
- Solar/Renewable/UPS-Micro Inverter System
- Charger
- Power Supply

Product Summary

VDS	650V
R _{DS(on)_typ}	0.39Ω
I _D	11A

100% DVDS Tested

100% Avalanche Tested



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
MCJH390N65GC	J390N65GC	TO-251	Tape&Reel	N/A	N/A	2500pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DS}	650	V
Continuous drain current ¹⁾ T _C = 25°C T _C = 100°C	I _D	11 7.0	A
Pulsed drain current (T _C = 25°C, t _p limited by T _{jmax})	I _{D pulse}	44	A
Avalanche energy, single pulse (L=60mH, R _g =30Ω)	E _{AS}	120	mJ
MOSFET dv/dt ruggedness	dv/dt	50	V/ns
Gate-Source voltage	V _{GS}	±30	V
Power dissipation (T _C = 25°C)	P _{tot}	109	W
Continuous diode forward current(T _C = 25°C)	I _S	11	A
Diode pulse current ²⁾ (T _C = 25°C)	I _{S pulse}	44	A
Recovery diode dv/dt ³⁾	dv/dt	50	V/ns
Operating junction and storage temperature	T _j , T _{stg}	-55...+150	°C

1) Limited by T_{j,max}. Maximum Duty Cycle D = 0.50; TO-220 equivalent

2) Pulse width t_p limited by T_{j,max}

3) Identical low side and high side switch with identical R_G

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R_{thJC}	1.15	°C/W
Thermal resistance, junction – ambient. Max	R_{thJA}	133	

Electrical Characteristic (at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	650	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	3.5	-	4.5	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=650V, V_{GS}=0V$ $T_C=25^\circ C$
		-	10	-		$T_C=150^\circ C$
Gate-source leakage current	I_{GSS}	-	0.3	80	nA	$V_{GS}=\pm 30V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.39	0.45	Ω	$V_{GS}=10V, I_D=5.5A,$ $T_C=25^\circ C$
		-	1	-		$T_C=150^\circ C$
Transconductance	g_{fs}	-	12	-	S	$V_{DS}=20V, I_D=5.5A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	790	-	pF	$V_{GS}=0V, V_{DS}=100V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	32	-		
Reverse Transfer Capacitance	C_{rss}	-	2	-		
Gate Total Charge	Q_G	-	22	-	nC	$V_{GS}=10V, V_{DS}=480V,$ $I_D=5.5A, f=1MHz$
Gate-Source charge	Q_{gs}	-	5.3	-		
Gate-Drain charge	Q_{gd}	-	8.8	-		
Gate-Drain charge	$V_{plateau}$	-	6	-	V	
Turn-on delay time	$t_{d(on)}$	-	20	-	ns	$T_j=25^\circ C, V_{GS}=10V,$ $I_D=5.5A, V_{DS}=400V,$ $R_g=25\Omega$
Rise time	t_r	-	15	-		
Turn-off delay time	$t_{d(off)}$	-	74	-		
Fall time	t_f	-	43	-		
Gate resistance	R_G	-	2.0	-	Ω	$f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	0.5	0.84	1	V	$V_{GS}=0V, I_{SD}=5.5A$
Body Diode Reverse Recovery Time	t_{rr}	-	218	-	ns	$I_{sd}=5.5A$ $dI/dt=100A/us$ $V_{ds}=100V$
Body Diode Reverse Recovery Charge	Q_{rr}	-	2.35	-	uC	

Typical Performance Characteristics

Fig 1. Output Characteristics (Tj=25°C)

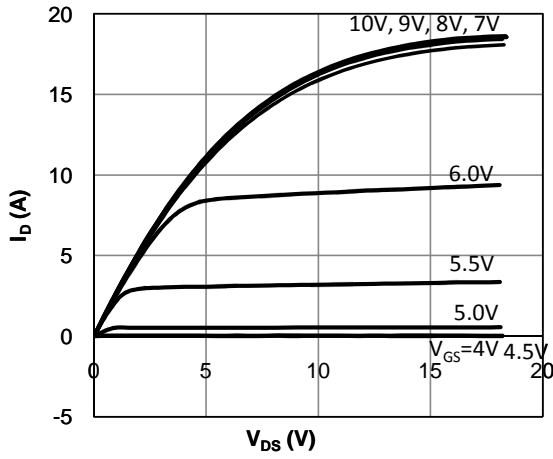


Fig 2. Output Characteristics (Tj=150°C)

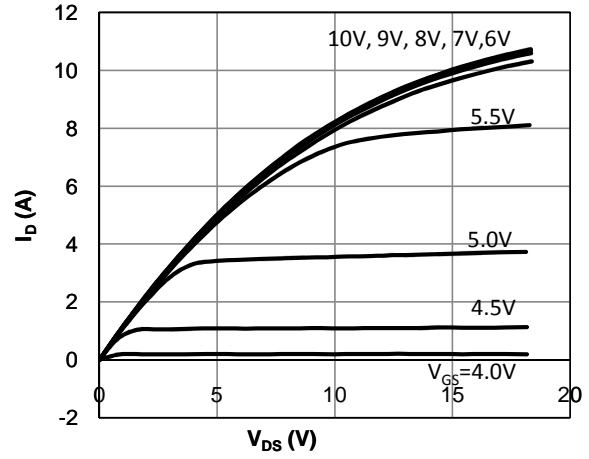


Fig 3: Transfer Characteristics

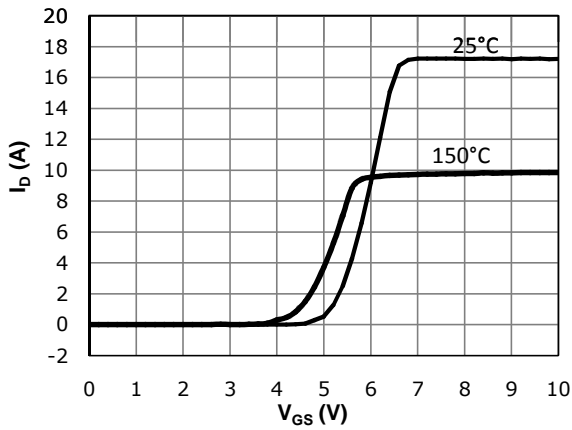


Fig 4: V_{TH} Vs T_j Temperature Characteristics

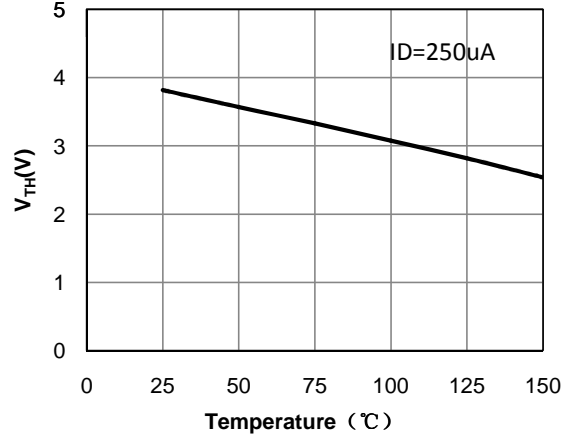


Fig 5: $R_{DS(on)}$ Vs I_{DS} Characteristics ($T_c=25^\circ\text{C}$)

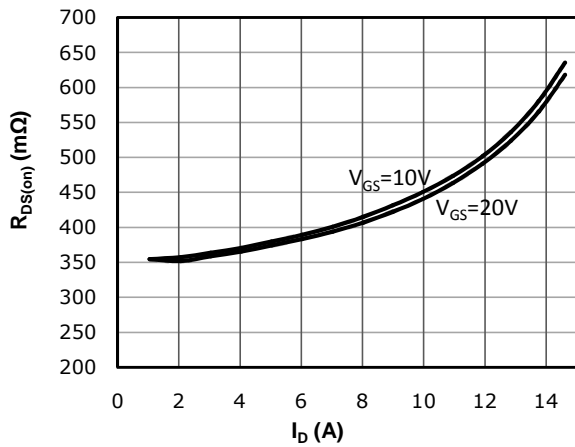


Fig 6: $R_{DS(on)}$ vs. Temperature

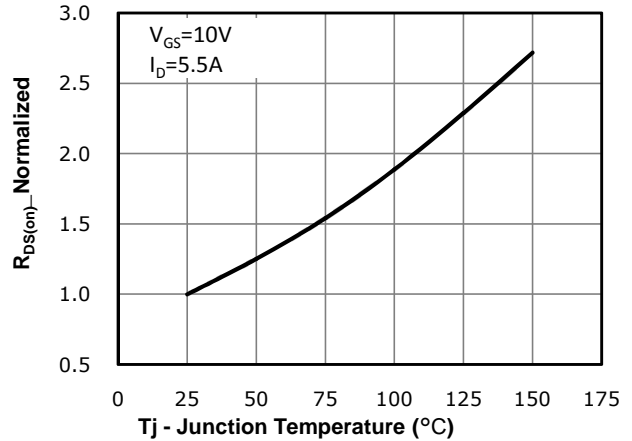


Fig 7: BVDSS vs. Temperature

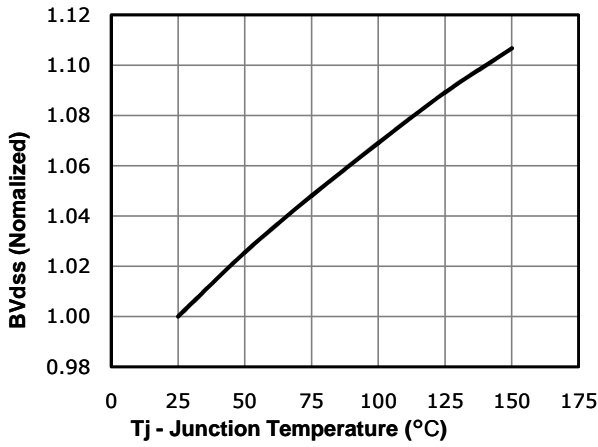


Fig 8: Rds(on) vs Gate Voltage

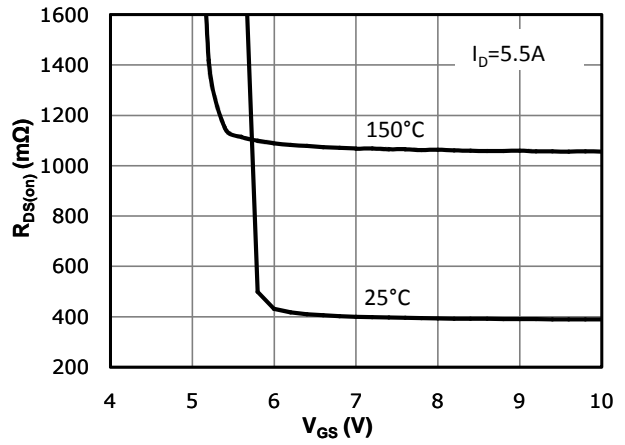


Fig 9: Body-diode Forward Characteristics

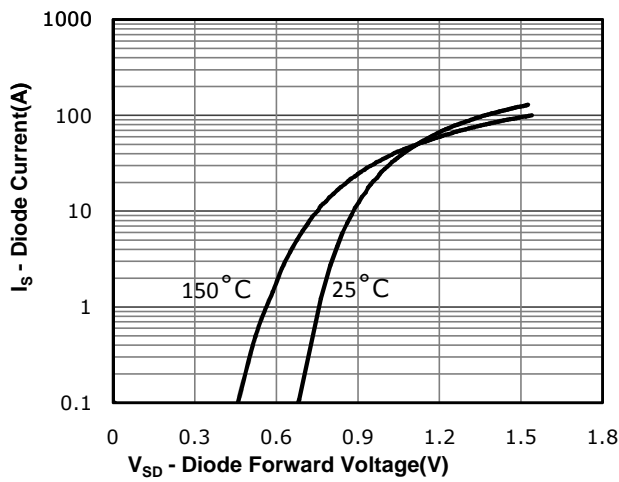


Fig 10: Gate Charge Characteristics

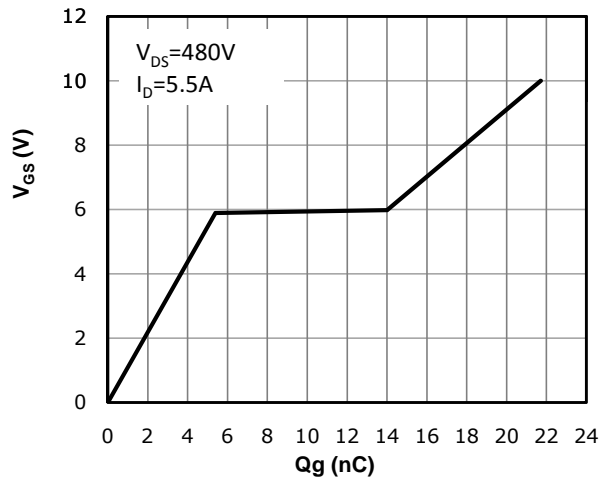


Fig 11: Capacitance Characteristics

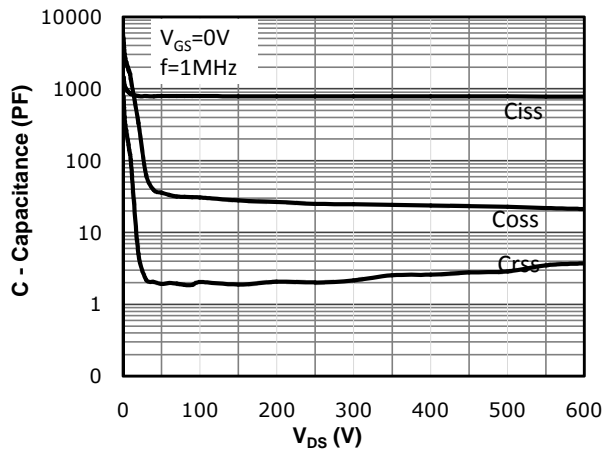
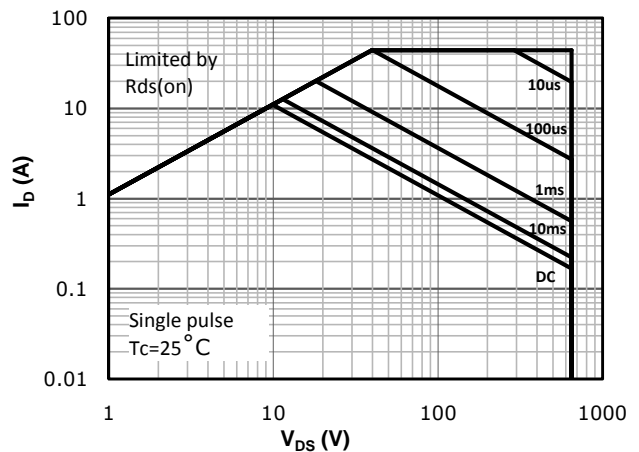
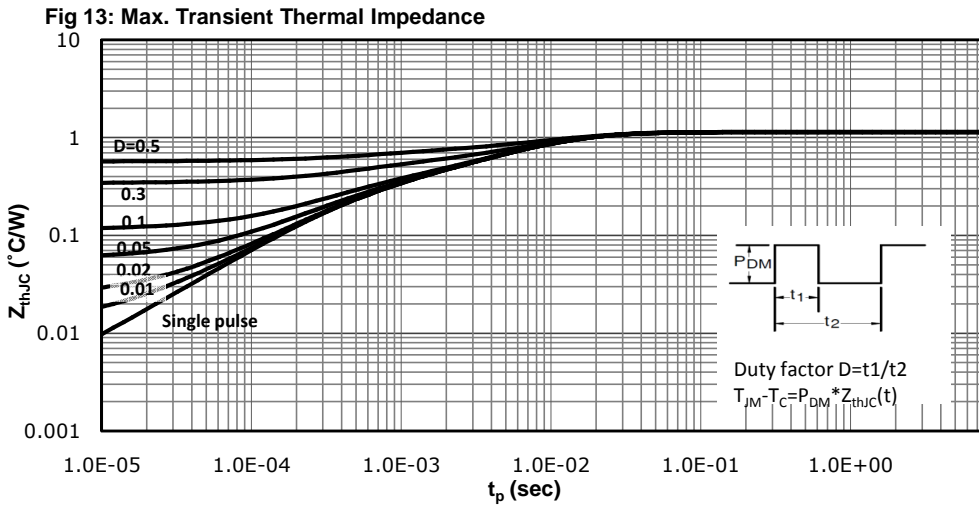


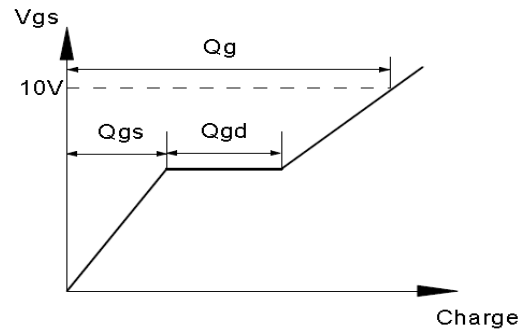
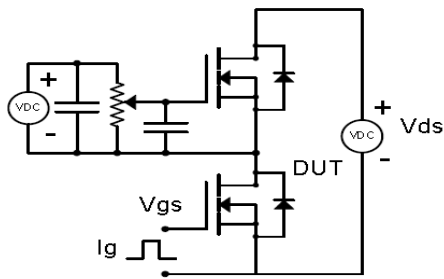
Fig 12: Safe Operating Area



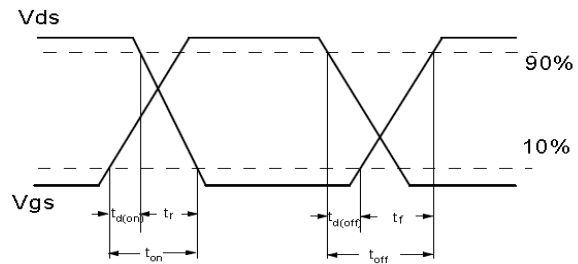
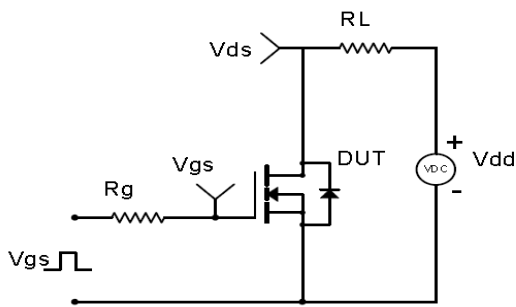


Test Circuit & Waveform

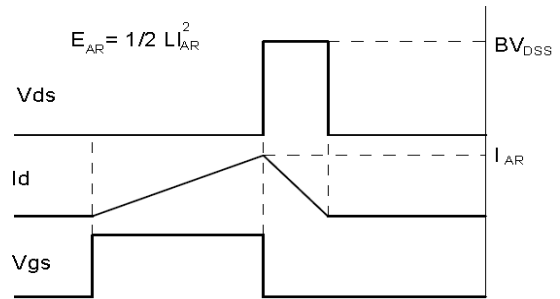
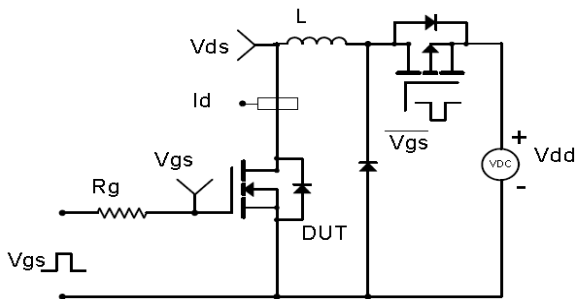
Gate Charge Test Circuit & Waveform



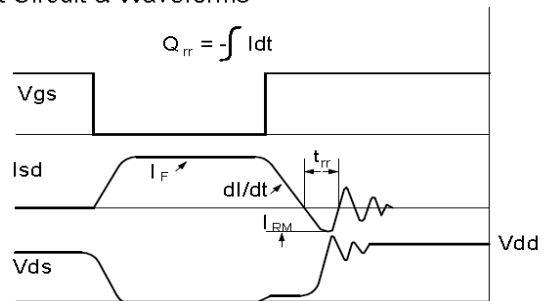
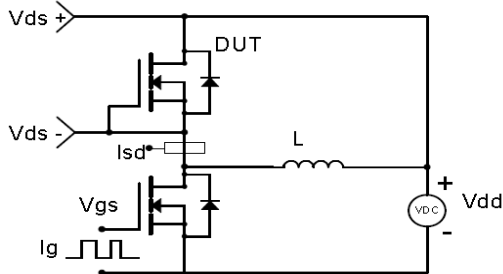
Resistive Switching Test Circuit & Waveforms



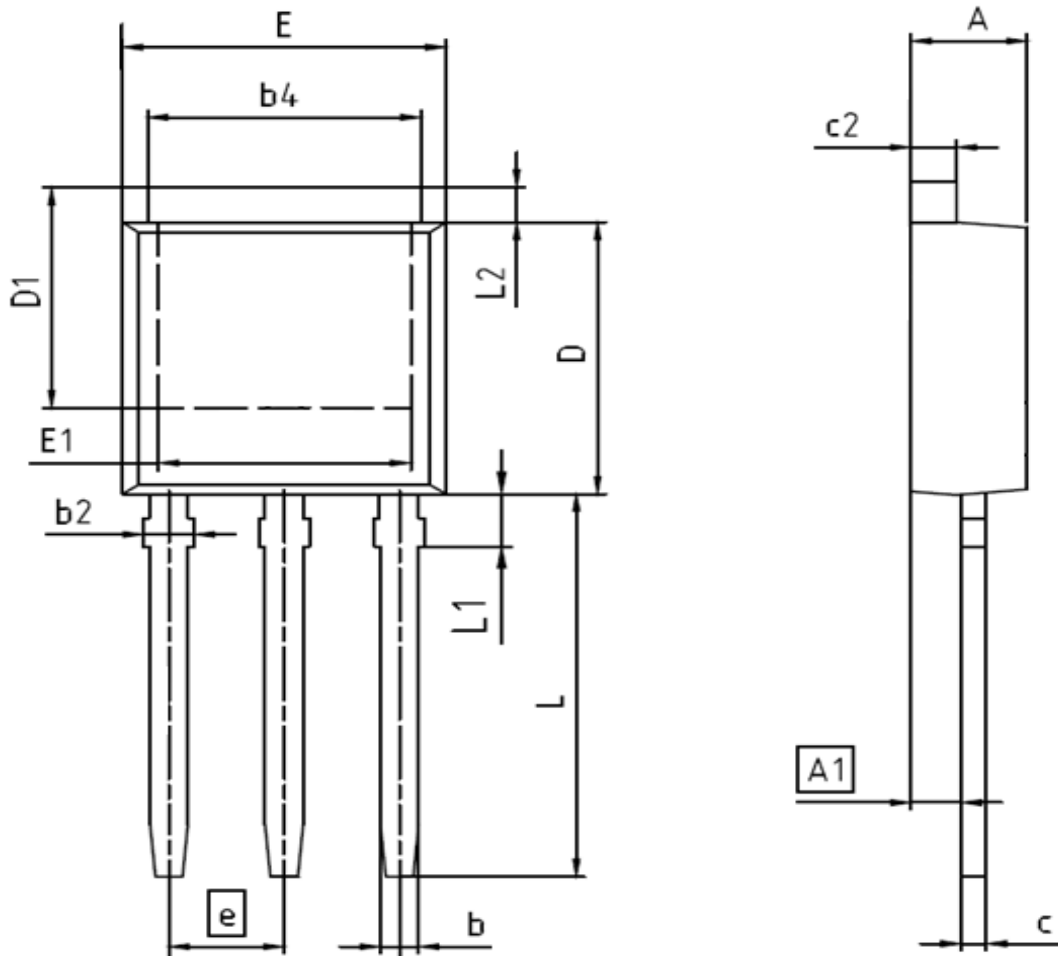
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO-251



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	6.30	6.90	0.248	0.272
B	5.20	6.30	0.205	0.248
B1	0.70	1.30	0.028	0.051
B2	6.80	7.40	0.268	0.291
C	2.10	2.50	0.083	0.098
C1	0.90	1.20	0.035	0.047
D	0.30	0.60	0.012	0.024
E	0.50	0.86	0.020	0.034
F	0.30	0.60	0.012	0.024
G	0.70	1.00	0.028	0.039
H	1.40	2.40	0.055	0.094
L*	9.00	9.80	0.354	0.386
M	5.10	5.50	0.201	0.217
N	2.09	2.49	0.082	0.098

*adjustable

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.